OPA8537RC

Infrared LED Chip

GaAs/GaAlAs

1. Material

Substrate GaAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltag	V_F		1.55	1.65	V	IF=30mA
Reverse Voltage	V_R	3			V	IR=10uA
Power	P_O	1.2	1.4		mW	IF=30mA
Wavelength	λ_P	850	863	880	nm	IF=30mA
	$\Delta\lambda$		30		nm	IF=30mA

※ Note : LED chip is mounted on TO-18 gold header without resin coati

4. Mechanical Data

(a) Diameter of Emission Area ---------- 128um
(b) Bottom Area -------------------- 210um X 330um
(c) Chip Thickness -------------------- 250um